

ABSTRACT OF THE DISCLOSURE

A device and process for the wet-chemical treatment of silicon using an etching liquid that contains water, nitric acid and hydrofluoric acid. The etching liquid is activated by introducing nitrogen oxide (NO_x) into the etching liquid, before being used for the wet-chemical treatment of silicon. The device consists of a first vessel in which silicon is subjected to a wet-chemical treatment with the aid of an etching liquid, a second vessel in which fresh etching liquid is held ready, and a connecting line between the first vessel and the second vessel, through which nitrogen oxides (NO_x) formed in the first vessel during the wet-chemical treatment are passed to the second vessel.